

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	10/074884	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:10
L2	674	(gate near2 substrate near2 capacitance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:10
L3	2	(gate near2 substrate near2 capacitance) with ((oxide near nitride) or oxynitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:12
L4	120	(gate near2 substrate near2 capacitance) and ((oxide near nitride) or oxynitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:13
L5	17	(gate near2 substrate near2 capacitance) and (((oxide near nitride) or oxynitride) near10 gate near10 dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:14
L6	1	(gate near2 substrate near2 capacitance).clm. and (((oxide near nitride) or oxynitride) near10 gate near10 dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:14
L7	0	(gate near2 substrate near2 capacitance).clm. and (((oxide near nitride) or oxynitride) near10 gate near10 dielectric) and (oxide near10 (gate adj dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:14
L8	11	(gate near2 substrate near2 capacitance) and (((oxide near nitride) or oxynitride) near10 gate near10 dielectric) and (oxide near10 (gate adj dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:15
L9	11	(gate near2 substrate near2 capacitance) and (((oxide adj nitride) or oxynitride) near10 gate near10 dielectric) and (oxide near10 (gate adj dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:15

L10	1	(gate near2 substrate near2 capacitance) same (((oxide adj nitride) or oxynitride) near10 gate near10 dielectric) and (oxide near10 (gate adj dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:16
L11	0	(gate near2 substrate near2 capacitance) same (((oxide adj nitride) or oxynitride) near10 gate near10 dielectric) same (oxide near10 (gate adj dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:15
L12	1	(gate near2 substrate near2 capacitance) same ((oxynitride) near10 gate near10 dielectric) and (oxide near10 (gate adj dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:16
L13	7	(gate near2 substrate near2 capacitance) and ((oxynitride) near10 gate near10 dielectric) and (oxide near10 (gate adj dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:17
L14	0	(gate near2 substrate near2 capacitance).clm. and ((oxynitride) near10 gate near10 dielectric) and (oxide near10 (gate adj dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:17
L15	45	(gate near2 substrate near2 capacitance).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:18
L16	7	(gate near2 substrate near2 capacitance).clm. and (gate near2 substrate near2 capacitance).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:18
L17	2	(gate near2 substrate near2 capacitance).clm. and (gate near2 substrate near2 capacitance).ab. and dielectric.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:19
L18	0	(gate near2 substrate near2 capacitance).clm. and (gate near2 substrate near2 capacitance).ab. and (gate adj dielectric).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:19
L19	5	(gate near2 substrate near2 capacitance).clm. and (gate adj dielectric).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:19

L38	12	I37 and (ozon or ozonated or ozonating or ozonation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:20
L39	12	I37 and (ozon or ozonated or ozonating or ozonation or ozonate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:21
L40	9	I37 and ((rinse or rinsing or rinsed) near10 (ozone or ozonated or ozonating or ozonation or ozonate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:21
L41	4	I37 and ((rinse or rinsing or rinsed) near10 (ozone or ozonated or ozonating or ozonation or ozonate)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:23
L42	0	I37 and ((rinse or rinsing or rinsed) near10 (ozone or ozonated or ozonating or ozonation or ozonate)).clm. and (gate adj dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:23
L43	0	I37 and ((rinse or rinsing or rinsed) near10 (ozone or ozonated or ozonating or ozonation or ozonate)).clm. and ((oxide near nitride) or oxynitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:23
L44	4	((rinse or rinsing or rinsed) near10 (ozone or ozonated or ozonating or ozonation or ozonate)).clm. and ((oxide near nitride) or oxynitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:24

L64	123	l63 and (ozone or ozonate or ozonated or ozonation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:25
L65	123	l63 and (ozone or ozonate or ozonated or ozonation or ozonating)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:27
L66	10	l63 and ((rinse or rinsing or rinsed) near10 (ozone or ozonate or ozonated or ozonation or ozonating))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:28
L67	6	l63 and ((rinse or rinsing or rinsed) near10 (ozone or ozonate or ozonated or ozonation or ozonating)) with (oxide or nitride or oxide-nitride or oxynitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 00:28